

IN THE CLAIMS

Please amend claim 8.

Please enter the pending claims as follows:

8. (Currently Amended) A gate electrode, comprising:

a gate layer disposed over above a substrate, ~~said gate layer having a substantially level upper surface;~~

~~a conductive layer disposed over said gate layer, said conductive layer extending beyond edges of said gate layer;~~

thin first spacers disposed ~~in contact with~~ adjacent to opposite sides of said gate layer ~~and below said conductive layer; and~~

thick second spacers disposed ~~in contact with~~ adjacent to said thin first spacers, said thick second spacers having vertical sidewalls each thick second spacer having a width throughout its height which is constant in a direction parallel with said thin first spacers, wherein ~~the~~ said gate layer, ~~the~~ said thin first spacers, and ~~the~~ said thick second spacers have approximately the same height; ~~and~~

a conductive layer disposed over said gate layer, said conductive layer extending laterally over said thin first spacers but not over sidewalls of said gate layer and not over said thick second spacers.

10. (Previously Presented) The gate electrode of claim 8, wherein said gate layer comprises polysilicon.

11. (Previously Presented) The gate electrode of claim 10, wherein said conductive layer comprises polycide.

12. (Previously Presented) The gate electrode of claim 8, wherein said thin first spacers comprise oxide.

14. (Previously presented) The gate electrode of claim 11, wherein said polycide comprises titanium salicide (TiSi<sub>2</sub>).

123. (Previously Presented) The gate electrode of claim 8, wherein said thick second spacers comprise nitride.

124. (Previously Presented) The gate electrode of claim 8, wherein the thin first spacers are at least as high as the thick second spacers.

125. (Previously Presented) The gate electrode of claim 8, wherein the thick second spacers are at least twice as thick as the thin first spacers.

126. (Previously Presented) The gate electrode of claim 125, wherein the thick second spacers are between 300 and 2000 Å thick.

127. (Previously Presented) The gate electrode of claim 126, wherein the thick second spacers are at least 800 Å thick.

128. (Previously Presented) The gate electrode of claim 125, wherein the thick second spacers are at least 800/100 times as thick as the thin first spacers.